



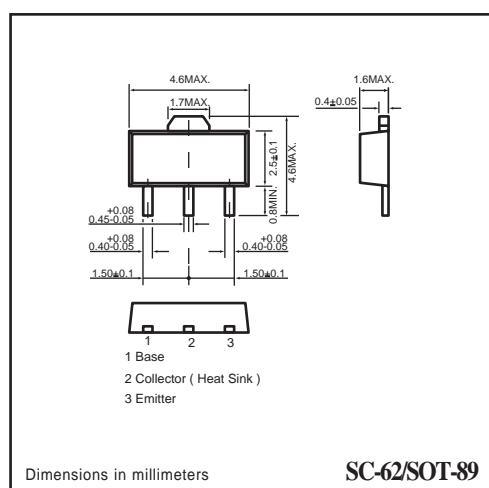
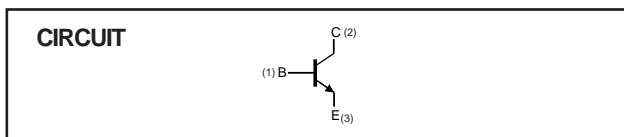
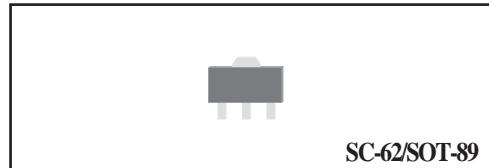
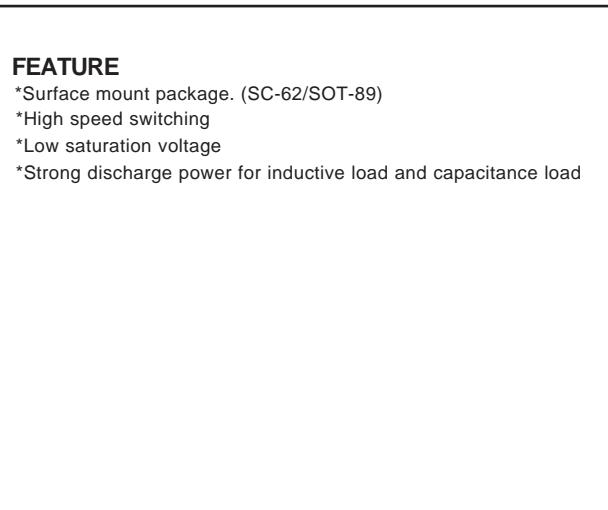
CHENMKO ENTERPRISE CO.,LTD

**SURFACE MOUNT
NPN Silicon Transistor**

VOLTAGE 60Volts CURRENT 3 Ampere

Lead free devices

CHT5824XPT



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	60	V
V_{CEO}	collector-emitter voltage	open base	–	60	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	3	A
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$; note 1 $T_{amb} \leq 25^\circ\text{C}$; note 2	–	500 2000	mW mW
T_{stg}	storage temperature		–55	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–55	+150	°C

Note

1. $P_w=100\text{mS}$
2. Each terminal mounted on a recommended land.

2007-06

RATING CHARACTERISTIC CURVES (CHT5824XPT)

CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$V_{CB} = 40\text{V}, I_E = 0$	—	1.0	uA
I_{CEO}	collector cut-off current	$V_{CE} = 50\text{V}, I_B = 0$	—	1.0	uA
I_{EBO}	emitter cut-off current	$V_{EB} = 4\text{V}, I_C = 0$	—	1.0	uA
h_{FE}	DC current gain	$I_C = 100 \text{ mA}; V_{CE} = 2\text{V}$	120	390	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = 2000 \text{ mA}; I_B = 200 \text{ mA}$	—	0.5	V
C_{ob}	collector output capacitance	$I_E = 0; V_{CB} = 10\text{V}; f = 1 \text{ MHz}$	20(typ)	—	pF
f_T	transition frequency	$I_C = 100 \text{ mA}; V_{CE} = 10\text{V}$ $f = 10 \text{ MHz}$	200(typ)	—	MHz

Note : Pulse test: $t_p \leq 300\mu\text{Sec}$; $\delta \leq 0.02$.